

NPN - MPS8099; PNP - MPS8599

Amplifier Transistors

Voltage and Current are Negative for PNP Transistors

MAXIMUM RATINGS

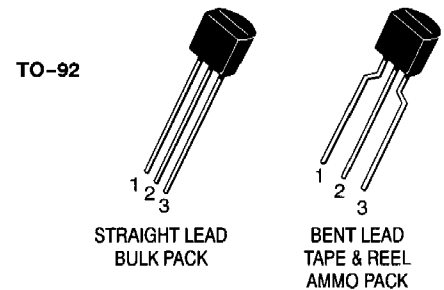
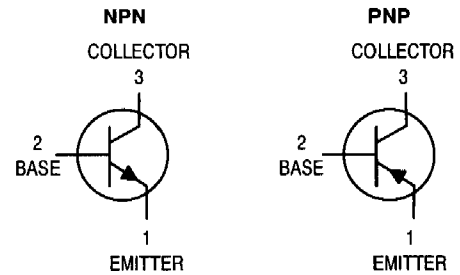
Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	80	Vdc
Collector - Base Voltage	V_{CBO}	80	Vdc
Emitter - Base Voltage	V_{EBO}	6.0	Vdc
Collector Current - Continuous	I_C	500	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.



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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (Note 2) ($I_C = 10\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	80	–	Vdc
Collector–Base Breakdown Voltage ($I_C = 100\text{ }\mu\text{Adc}$, $I_E = 0$)	$V_{(BR)CBO}$	80	–	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10\text{ }\mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	6.0	–	Vdc
Collector Cutoff Current ($V_{CE} = 60\text{ Vdc}$, $I_B = 0$)	I_{CES}	–	0.1	μAdc
Collector Cutoff Current ($V_{CB} = 80\text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	0.1	μAdc
Emitter Cutoff Current ($V_{EB} = 6.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	0.1	μAdc

ON CHARACTERISTICS (Note 2)

DC Current Gain ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 100\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	100 100 75	300 – –	–
Collector–Emitter Saturation Voltage ($I_C = 100\text{ mAdc}$, $I_B = 5.0\text{ mAdc}$) ($I_C = 100\text{ mAdc}$, $I_B = 10\text{ mAdc}$)	$V_{CE(sat)}$	– –	0.4 0.3	Vdc
Base–Emitter On Voltage ($I_C = 10\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$)	$V_{BE(on)}$	0.6	0.8	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ($I_C = 10\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	150	–	MHz
Output Capacitance ($V_{CB} = 5.0\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	–	8.0	pF
Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	–	30	pF

2. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle = 2.0%.